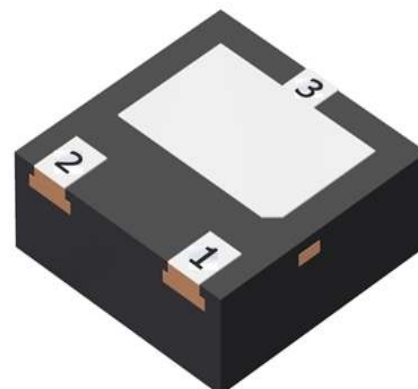


LTVS20H7.0T5G

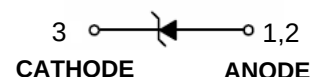
LTVS20H7.0T5G

Features

- 7V uni-directional ESD diode
- Low clamping voltage
- Complies with IEC 61000-4-2 standards:
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
- RoHS Compliant



DFN2020-3



Ordering information

Device	Marking	Packing
LTVS20H7.0T5G	C2	DFN2020-3

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	2800	W
Peak Pulse Current (8/20 μs)	I _{PP}	165	A
Operating Temperature Range	T _J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			7.0	V	
Breakdown Voltage	V _{BR}	7.6		9	V	I _T = 1mA
Reverse Leakage Current	I _R			2	μA	V _R = 7.0V
Clamping Voltage	V _C			10	V	I _{PP} = 60A (8 x 20 μs pulse)
Clamping Voltage	V _C			17	V	I _{PP} = 165A (8 x 20 μs pulse)
Forward Voltage	V _F		0.75	1.2	V	I _F = 10mA

Note: Electrical parameters are only for die, performance may alter after assembly.

LTVS20H7.0T5G

Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)

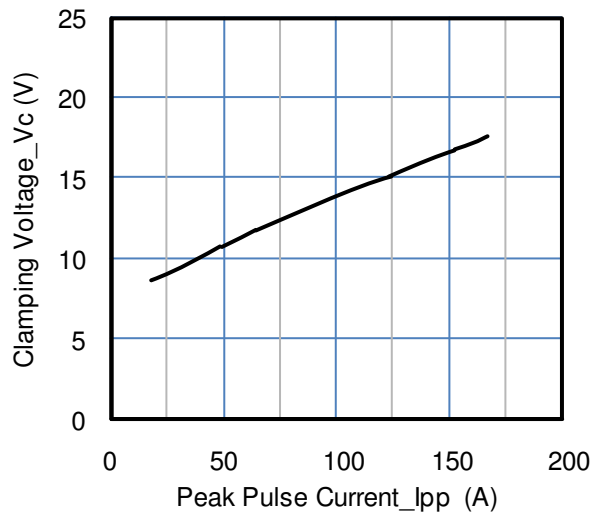


Fig 1. Clamping Voltage vs. Peak Pulse Current

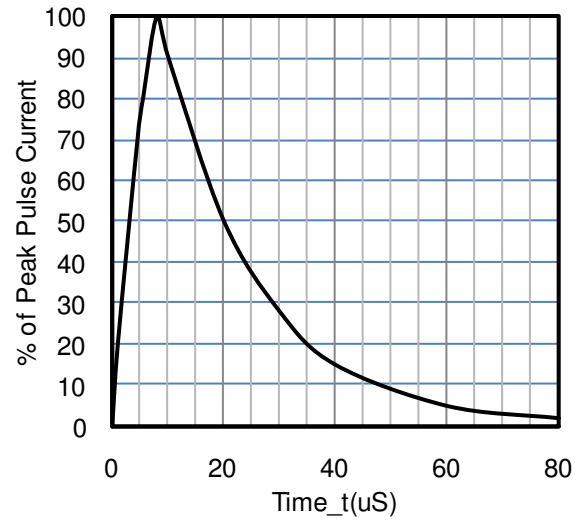


Fig 2. 8 X 20uS Pulse Waveform

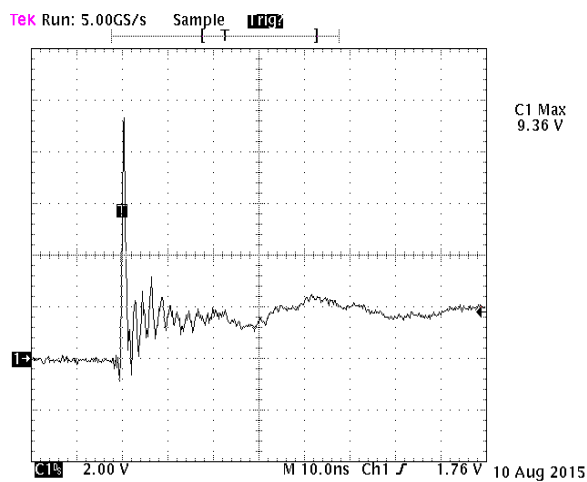


Fig 3. ESD Clamping Voltage
Positive 8 kV Contact per IEC61000-4-2

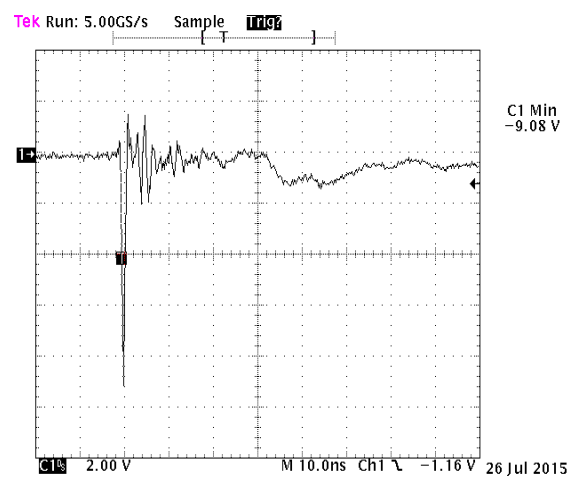
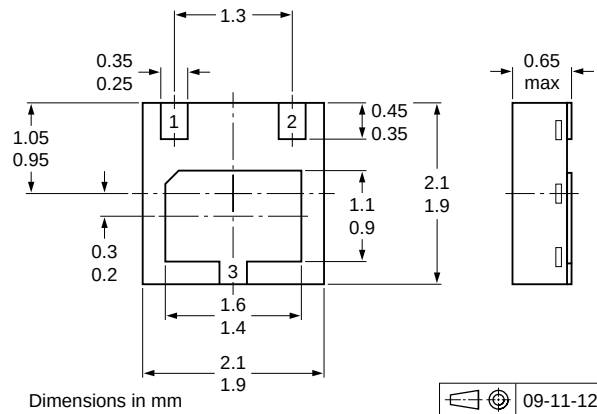


Fig 4. ESD Clamping Voltage
Negative 8 kV Contact per IEC61000-4-2

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Suggested solder pad layout

